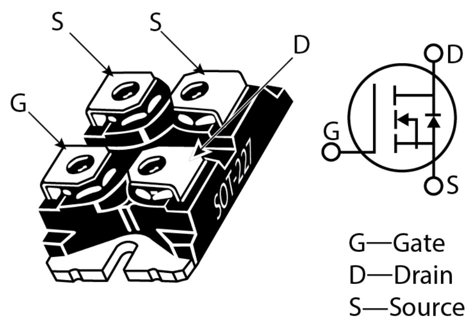
MSC080SMA120J

Silicon Carbide N-Channel Power MOSFET

Product Overview

The silicon carbide (SiC) power MOSFET product line from Microsemi increases the performance over silicon MOSFET and silicon IGBT solutions while lowering the total cost of ownership for high-voltage applications. The MSC080SMA120J device is a 1200 V, 80 mΩ SiC MOSFET in an SOT-227 package.



Features

The following are key features of the MSC080SMA120J device:

- Low capacitances and low gate charge
- Fast switching speed due to low internal gate resistance (ESR)
- Stable operation at high junction temperature, $T_{J(max)}$ = 175 °C
- Fast and reliable body diode
- Superior avalanche ruggedness
- RoHS compliant
- Isolated voltage to 2500 V

Benefits

The following are benefits of the MSC080SMA120J device:

- High efficiency to enable lighter, more compact system
- Simple to drive and easy to parallel
- Improved thermal capabilities and lower switching losses
- Eliminates the need for external freewheeling diode
- Lower system cost of ownership

Applications

The MSC080SMA120J device is designed for the following applications:

- PV inverter, converter, and industrial motor drives
- Smart grid transmission and distribution
- Induction heating and welding
- H/EV powertrain and EV charger
- Power supply and distribution

1. Device Specifications

This section shows the specifications of the MSC080SMA120J device.

1.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings of the MSC080SMA120J device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain source voltage	1200	V
I_D	Continuous drain current at T_C = 25 °C	31	A
	Continuous drain current at T_C = 100 °C	22	
I_{DM}	Pulsed drain current[1]	77	
V_{GS}	Gate-source voltage	23 to –10	V
P_D	Total power dissipation at T_C = 25 °C	143	W
	Linear derating factor	0.95	W/°C

Note:

1. Repetitive rating: pulse width and case temperature limited by maximum junction temperature.

The following table shows the thermal and mechanical characteristics of the MSC080SMA120J device.

Table 1-2. Thermal and Mechanical Characteristics

Symbol	Characteristic/Test Conditions	Min	Typ	Max	Unit
$R_{θJC}$	Junction-to-case thermal resistance		0.70	1.05	°C/W
T_J	Operating junction temperature	–55		175	°C
T_{STG}	Storage temperature	–55		150	
T_L	Soldering temperature for 10 seconds (1.6 mm from case)			300	
$V_{ISOLATION}$	RMS voltage (50 Hz–60 Hz sinusoidal waveform from terminals to mounting base for 1 minute)	2500			V
	Mounting torque, M4 screw			10	lbf-in
				1.1	N-m
Wt	Package weight		1.03		oz
			29.2		g

1.2 Electrical Performance

The following table shows the static characteristics of the MSC080SMA120J device. T_J = 25 °C unless otherwise specified.

Table 1-3. Static Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 100 μA	1200			V
$R_{DS(on)}$	Drain-source on resistance [1]	V_{GS} = 20 V, I_D = 15 A		80	100	mΩ
$V_{GS(th)}$	Gate-source threshold voltage	V_{GS} = V_{DS} , I_D = 1 mA	1.9	2.8		V
$\Delta V_{GS(th)}/\Delta T_J$	Threshold voltage coefficient	V_{GS} = V_{DS} , I_D = 1 mA		–4.5		mV/°C
I_{DSS}	Zero gate voltage drain current	V_{DS} = 1200 V, V_{GS} = 0 V			100	μA
		V_{DS} = 1200 V, T_J = 125 °C, V_{GS} = 0 V			500	
I_{GSS}	Gate-source leakage current	V_{GS} = 20 V/–10 V			±100	nA

Note:

1. Pulse test: pulse width < 380 μs, duty cycle < 2%.

The following table shows the dynamic characteristics of the MSC080SMA120J device. T_J = 25 °C unless otherwise specified.

Table 1-4. Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input capacitance	V_{GS} = 0 V, V_{DD} = 1000 V V_{AC} = 25 mV, f = 1 MHz		838		pF
C_{rss}	Reverse transfer capacitance			9		
C_{oss}	Output capacitance			84		
Q_g	Total gate charge	V_{GS} = –5 V/20 V, V_{DD} = 800 V I_D = 15 A		64		nC
Q_{gs}	Gate-source charge			12		
Q_{gd}	Gate-drain charge			19		

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
...........continued						
$t_{d(on)}$	Turn-on delay time	V_{DD} = 850 V, V_{GS} = –5 V/20 V I_D = 20 A, $R_{g(ext)}$ = 4 Ω Freewheeling diode = MSC080SMA120J (V_{GS} = –5V) (reference Fig. 1-17)		14		ns
t_r	Voltage rise time			14		
$t_{d(off)}$	Turn-off delay time			19		
t_f	Voltage fall time			13		
E_{on}	Turn-on switching energy			350		μJ
E_{off}	Turn-off switching energy			65		
ESR	Equivalent series resistance	f = 1 MHz, 25 mV, drain short		1.9		Ω
SCWT	Short circuit withstand time	V_{DS} = 960 V, V_{GS} = 20 V		3		μS
E_{AS}	Avalanche energy, single pulse	V_{DS} = 150 V, I_D = 15 A		1000		mJ

The following table shows the body diode characteristics of the MSC080SMA120J device. T_J = 25 °C unless otherwise specified.

Table 1-5. Body Diode Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{SD}	Diode forward voltage	I_{SD} = 15 A, V_{GS} = 0 V		4.0		V
		I_{SD} = 15 A, V_{GS} = –5 V		4.2		
t_{rr}	Reverse recovery time	I_{SD} = 15 A, V_{GS} = –5 V V_{DD} = 800 V, dI/dt = –1000 A/μs		34		ns
Q_{rr}	Reverse recovery charge			200		nC
I_{RRM}	Reverse recovery current			6.5		A

1.3 Typical Performance Curves

This section shows the typical performance curves of the MSC080SMA120J device.

Figure 1-1. Drain Current vs. V_{DS} at T_J

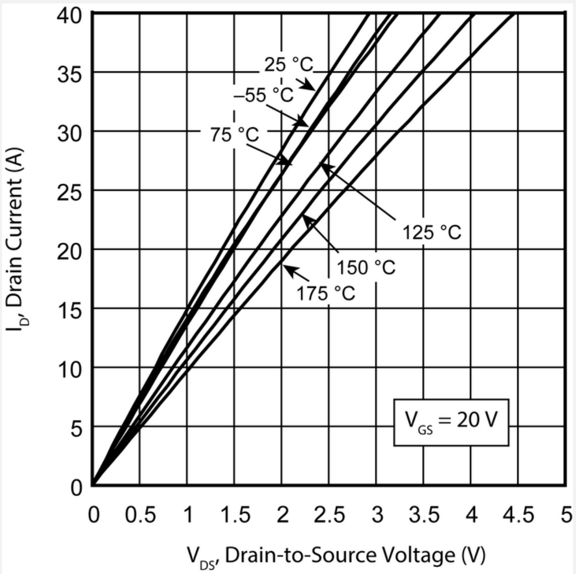


Figure 1-2. Drain Current vs. V_{DS} at V_{GS}

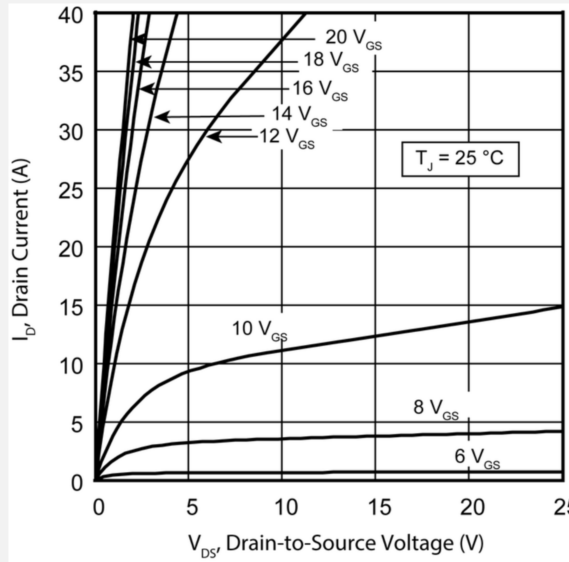


Figure 1-3. Drain Current vs. V_{DS} at V_{GS}

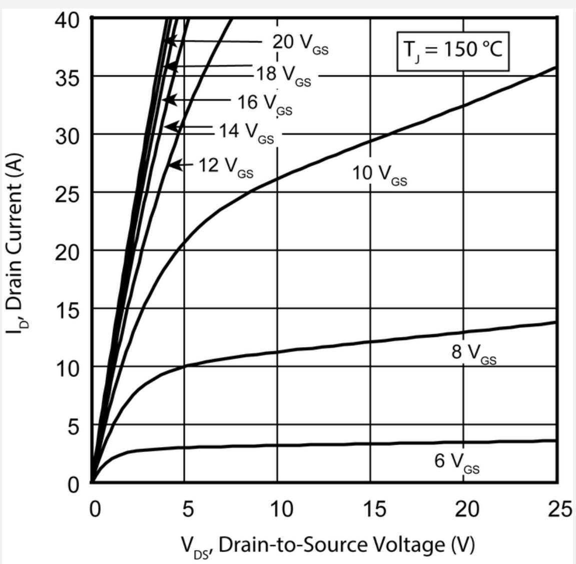


Figure 1-4. Drain Current vs. V_{DS} at V_{GS}

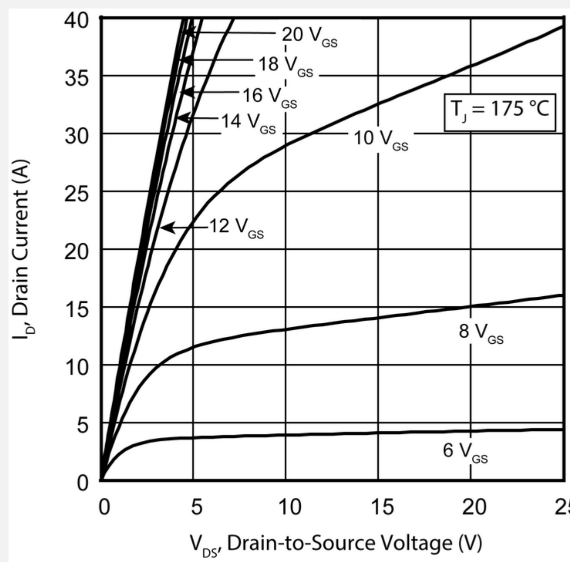


Figure 1-5. $R_{DS(on)}$ vs. Junction Temperature

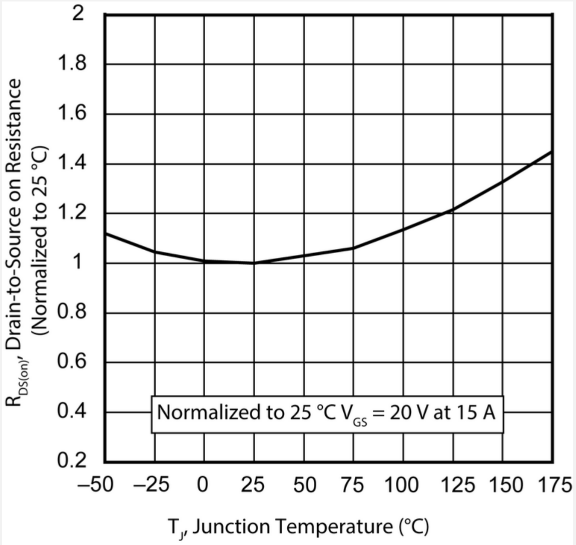


Figure 1-6. Gate Charge Characteristics

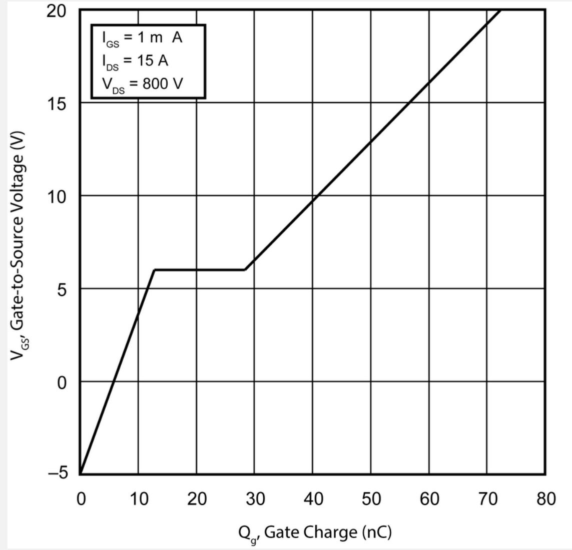


Figure 1-7. Capacitance vs. Drain-to-Source Voltage

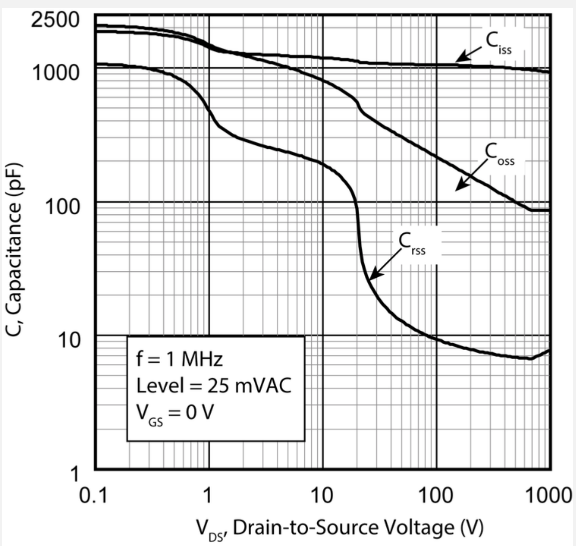


Figure 1-8. I_D vs. V_{DS} 3rd Quadrant Conduction

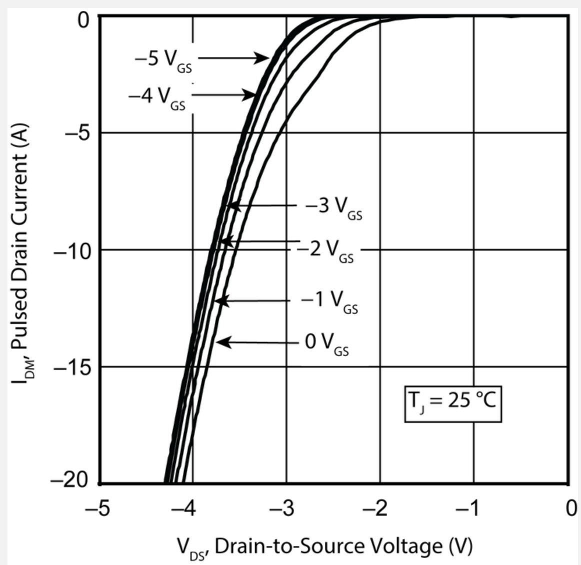


Figure 1-9. I_D **vs.** V_{DS} **3rd Quadrant Conduction**

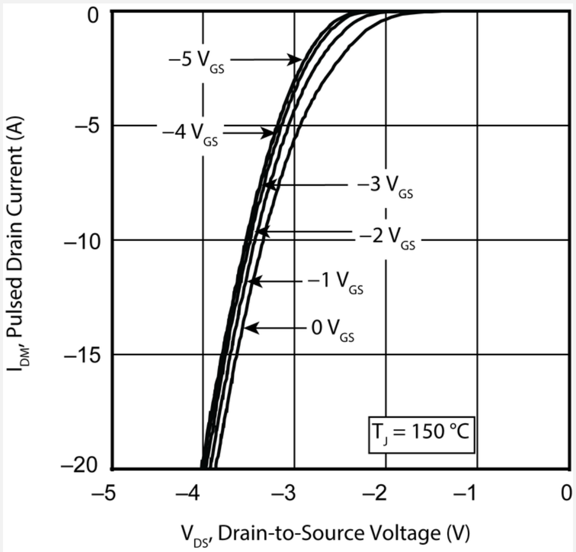


Figure 1-10. Switching Energy Eon vs. V_{DS} **&** I_D

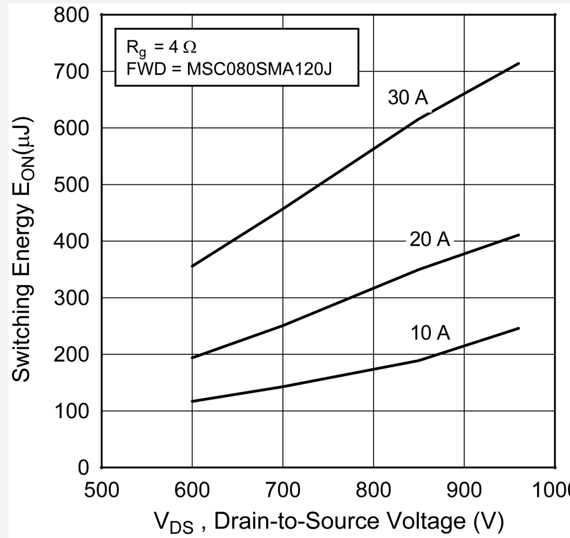


Figure 1-11. Switching Energy Eoff vs. V_{DS} **&** I_D

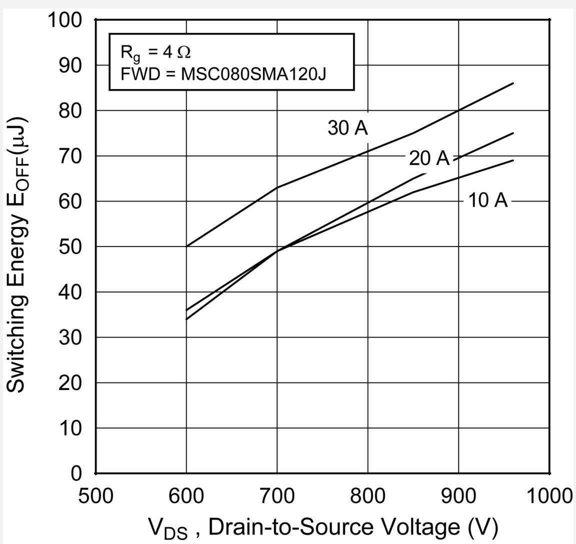


Figure 1-12. Switching Energy vs. R_g

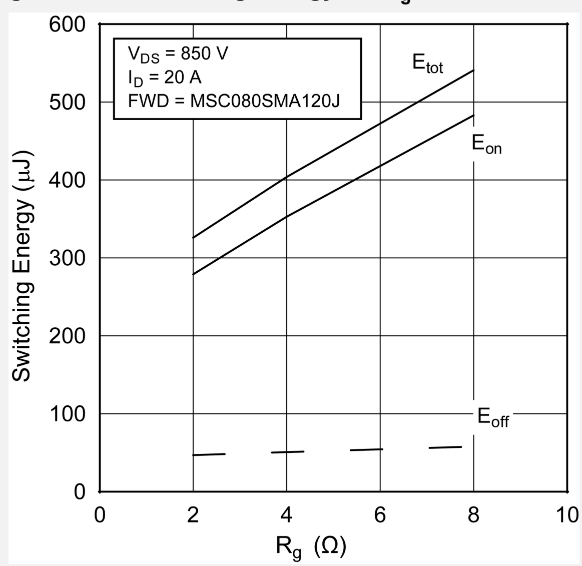


Figure 1-13. Switching Energy vs. Temperature

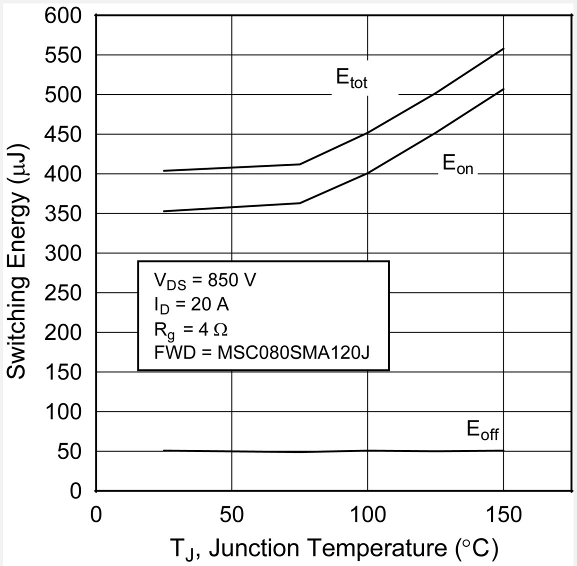


Figure 1-14. Threshold Voltage vs. Junction Temp.

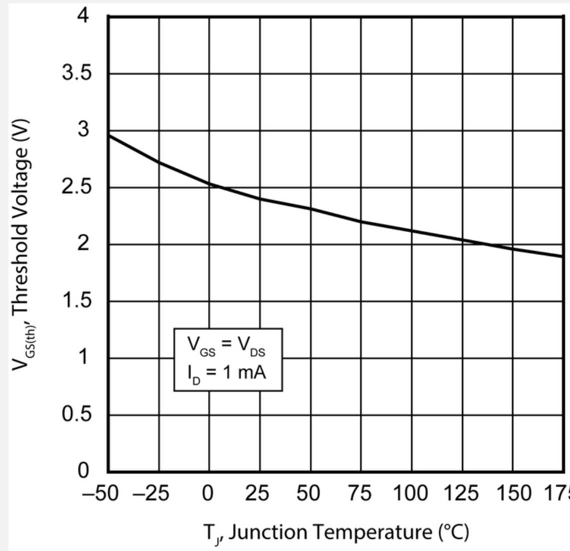


Figure 1-15. Forward Safe Operating Area

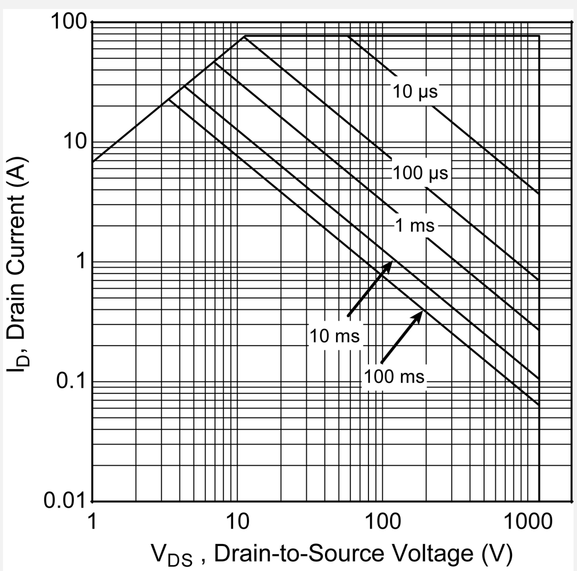
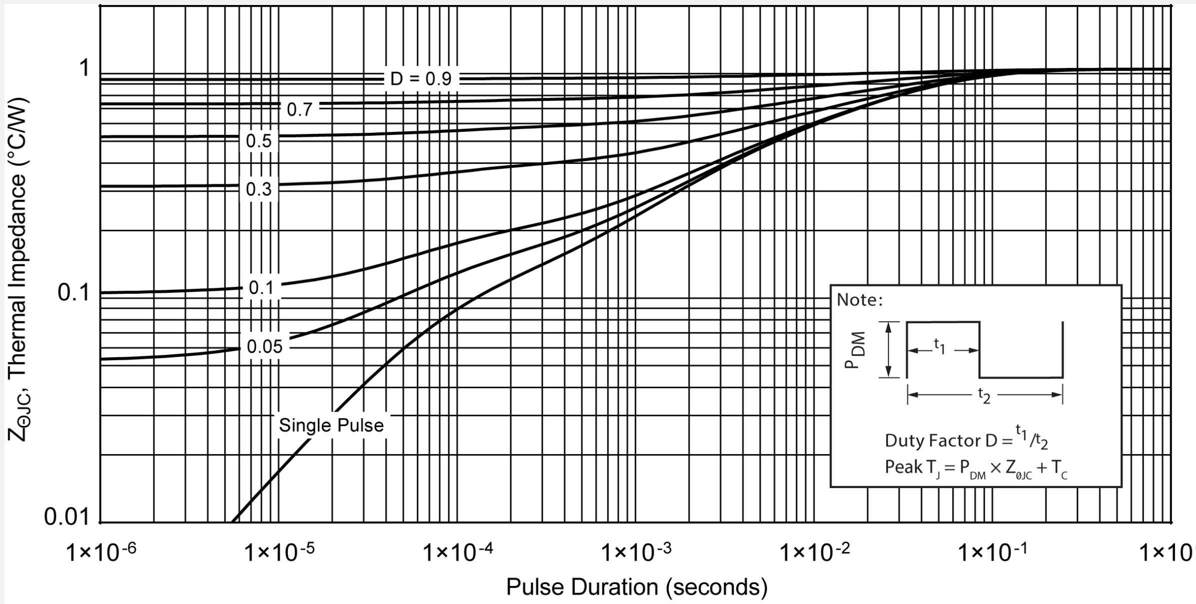
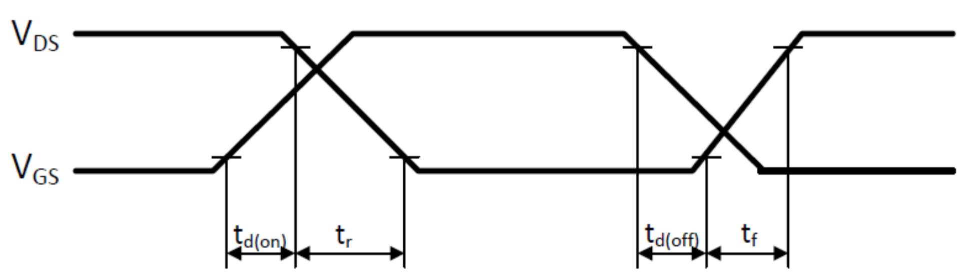


Figure 1-16. Maximum Transient Thermal Impedance



The following figure shows the switching waveform diagram of the MSC080SMA120J device.

Figure 1-17. Switching Waveform



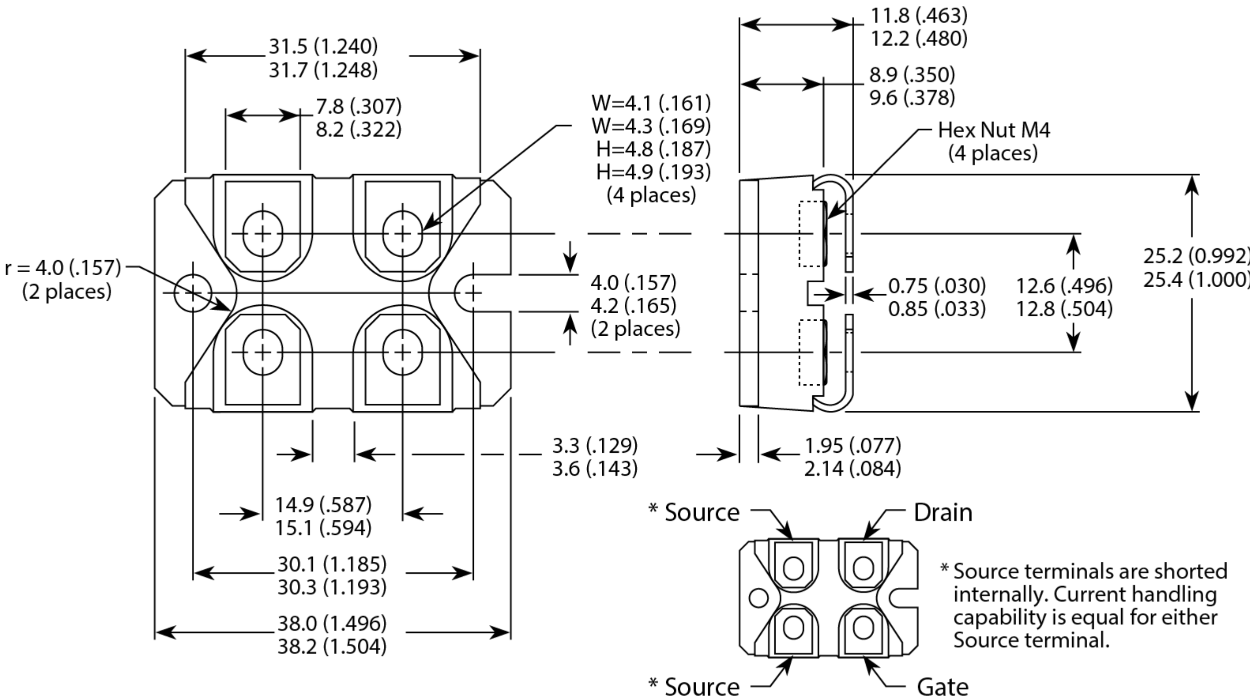
2. Package Specification

This section shows the package specification of the MSC080SMA120J device.

2.1 Package Outline Drawing

The following figure illustrates the SOT-227 package outline of the MSC080SMA120J device. The dimensions in the figure below are in millimeters and (inches).

Figure 2-1. Package Outline Drawing



3. Revision History

Table 3-1. Revision History

Revision	Date	Description
A	06/2021	Document migrated from Microsemi template to Microchip template; Assigned Microchip literature number DS-00004138A,which replaces the previous Microsemi literature number 050-7767.
Initial release (Microsemi Revision A)	02/2020	Document created.

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